

March 2013

FDP12N50NZ / FDPF12N50NZ N-Channel UniFETTM II MOSFET 500 V, 11.5 A, 520 m Ω

Features

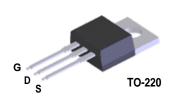
- $R_{DS(on)} = 460 \text{ m}\Omega \text{ (Typ.)} @ V_{GS} = 10 \text{ V}, I_D = 5.75 \text{ A}$
- Low Gate Charge (Typ. 23 nC)
- Low C_{rss} (Typ. 14 pF)
- 100% Avalanche Tested
- · ESD Improved Capability
- · RoHS Compliant

Applications

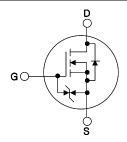
- LCD/LED/PDP TV
- Lighting
- Uninterruptible Power Supply

Description

UniFETTM II MOSFET is Fairchild Semiconductor[®]'s high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2kV HBM surge stress. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.







MOSFET Maximum Ratings T_C = 25°C unless otherwise noted*

Symbol		Parameter		FDP12N50NZ	FDPF12N50NZ	Unit	
V _{DSS}	Drain to Source Voltage	Orain to Source Voltage			500		
V _{GSS}	Gate to Source Voltage	Gate to Source Voltage		±25		V	
ı	Drain Current	- Continuous (T _C = 25°C)		11.5	11.5*	۸	
ID	Drain Current	- Continuous (T _C = 100°C)		6.9	6.9*	Α	
I _{DM}	Drain Current	- Pulsed	(Note 1)	46	46*	Α	
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	560		mJ	
I _{AR}	Avalanche Current		(Note 1)	11.5		Α	
E _{AR}	Repetitive Avalanche En	ergy	(Note 1)	17		mJ	
dv/dt	Peak Diode Recovery dv	/dt	(Note 3)	4.5		V/ns	
D	Dawan Diagination	$(T_C = 25^{\circ}C)$		170	42	W	
P_{D}	Power Dissipation - Derate above 25°C			1.37	0.33	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range			-55 t	o +150	°С	
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			3	300	°C	

*Dran current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FDP12N50NZ	FDPF12N50NZ	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max. 0.73 3.0			
$R_{\theta CS}$	Thermal Resistance, Case to Sink Typ 0.5 -		°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. 62.5 62.5			

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP12N50NZ	FDP12N50NZ	TO-220	-	-	50
FDPF12N50NZ	FDPF12N50NZ	TO-220F	=	=	50

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu A$, $V_{GS} = 0V$, $T_J = 25^{\circ}C$	500	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	-	0.5	-	V/°C
1	Zero Gate Voltage Drain Current	$V_{DS} = 500V, V_{GS} = 0V$	-	-	1	^
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 400V, T_{C} = 125^{\circ}C$	-	-	10	μА
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 25V, V_{DS} = 0V$	-	-	±10	μΑ

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10V, I_D = 5.75A$	•	0.46	0.52	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 20V, I_{D} = 5.75A$	i	12	•	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 05V V 0V		-	945	1235	pF
C _{oss}	Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V$		-	155	205	pF
C _{rss}	Reverse Transfer Capacitance	1 - 111112		-	14	20	pF
Qg	Total Gate Charge at 10V	V _{DS} = 400V, I _D = 11.5A		-	23	30	nC
Q _{gs}	Gate to Source Gate Charge	V _{GS} = 10V		-	5.5	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		(Note 4)	-	9.6	-	nC

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	V _{DD} = 250V, I _D = 11.5A	-	20	50	ns
t _r	Turn-On Rise Time	$R_G = 25\Omega$	-	50	110	ns
t _{d(off)}	Turn-Off Delay Time		-	60	130	ns
t _f	Turn-Off Fall Time	(Note	4) -	45	100	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	11.5	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	46	Α
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_{SD} = 11.5A$	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _{SD} = 11.5A	-	315	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	-	2.0	-	μС

Notos

- Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L = 8.5mH, I_{AS} = 11.5A, V_{DD} = 50V, R_{G} = 25 $\!\Omega$, Starting T_{J} = 25 $^{\circ}C$
- 3. $I_{SD} \le 11.5 A, \ di/dt \le 200 A/\mu s, \ V_{DD} \le BV_{DSS}, \ Starting \ T_J = 25^{\circ}C$
- 4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

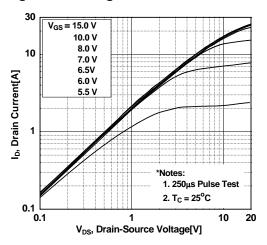


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

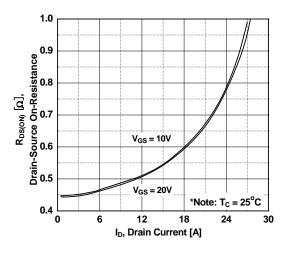


Figure 5. Capacitance Characteristics

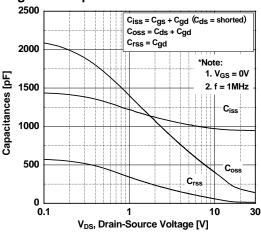


Figure 2. Transfer Characteristics

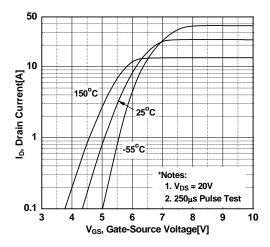


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

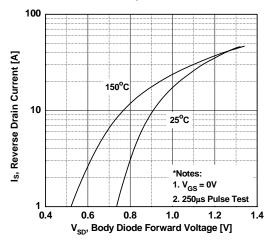
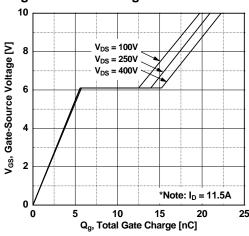


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

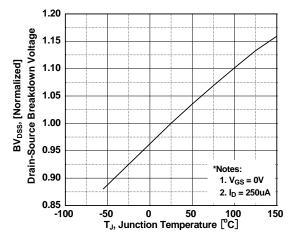


Figure 9. Maximum Safe Operating Area - FDPF12N50NZ

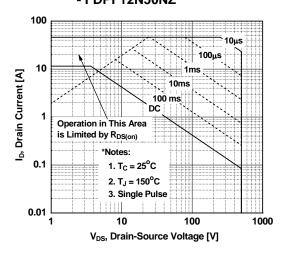


Figure 8. On-Resistance Variation vs. Temperature

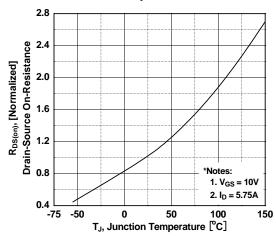


Figure 10.Maximum Safe Operating Area - FDP12N50NZ

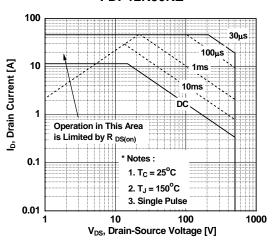
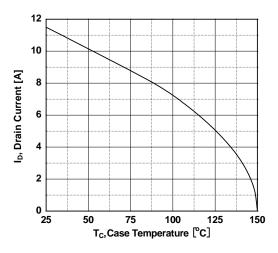


Figure 11. Maximum Drain Current vs. Case Temperature



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve - FDP12N50NZ

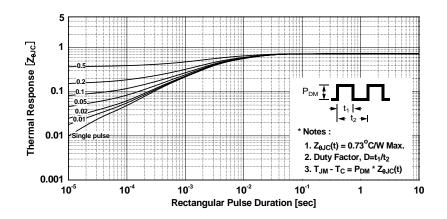
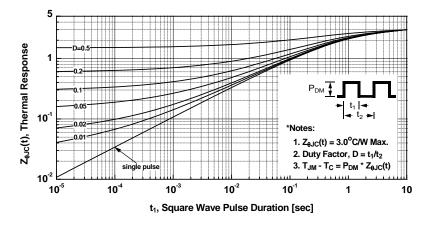
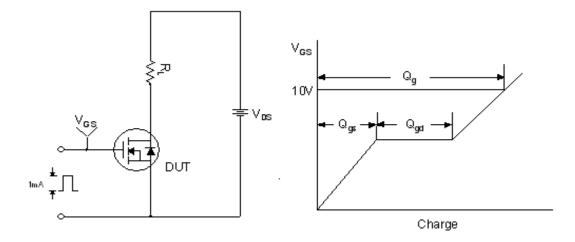


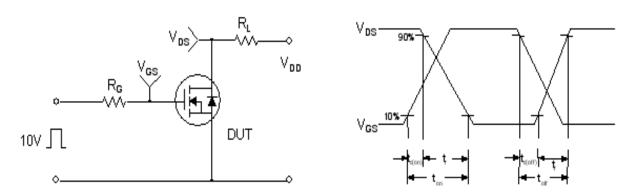
Figure 13. Transient Thermal Response Curve - FDPF12N50NZ



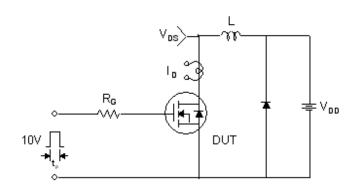
Gate Charge Test Circuit & Waveform

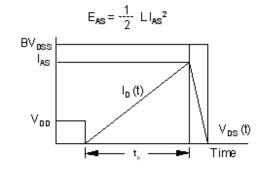


Resistive Switching Test Circuit & Waveforms

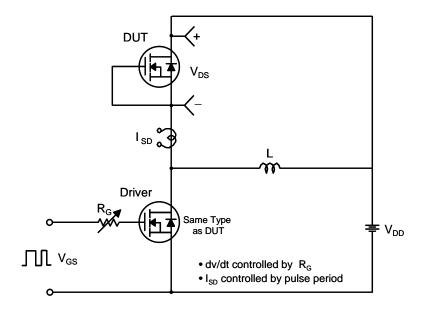


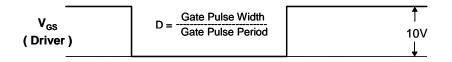
Unclamped Inductive Switching Test Circuit & Waveforms

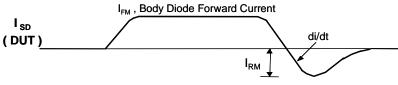




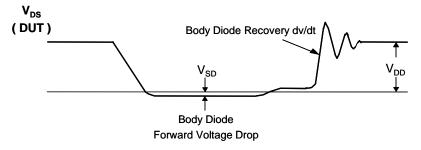
Peak Diode Recovery dv/dt Test Circuit & Waveforms





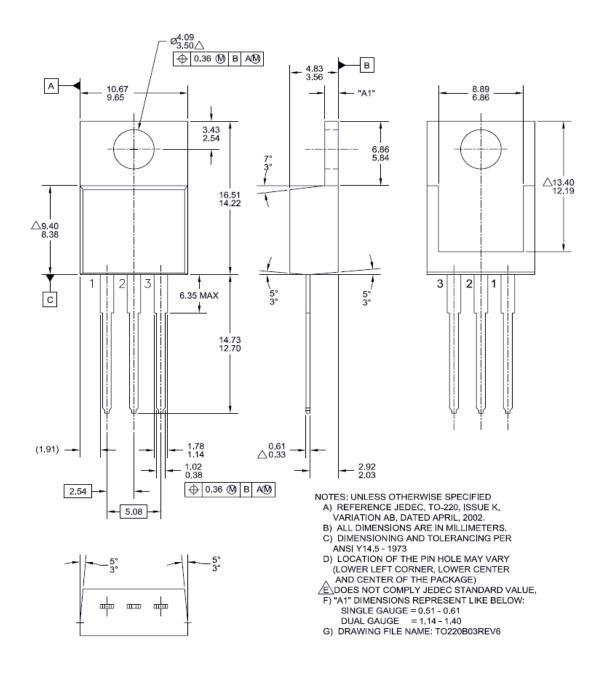


Body Diode Reverse Current



Mechanical Dimensions

TO-220B03



Mechanical Dimensions TO-220M03 2.74 2.34 10.36 Α 9.96 Ø3.28 7.00 3.40 3.08 (0.70) 3.20 SEE NOTE "F" SEE NOTE "F" 6.88 6.48 \oplus 1 X 45° 16.07 15.67 16.00 15.60 (3.23) B 3 1 1.47 2.96 1.24 2.14 2.56 0.90 10.05 0.70 9.45 ⊕ 0.50 M 30° 0.45 0.60 0.25 0.45 2.54 2.54 NOTES: A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A. DOES NOT COMPLY EIAJ STD. VALUE. C. ALL DIMENSIONS ARE IN MILLIMETERS. D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS. 4.90 ∠B 4.50 E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994. F. OPTION 1 - WITH SUPPORT PIN HOLE. OPTION 2 - NO SUPPORT PIN HOLE. G. DRAWING FILE NAME: TO220M03REV3 Dimensions in Millimeters





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